

ECEN325: Electronics

Spring 2024

Current Mirrors



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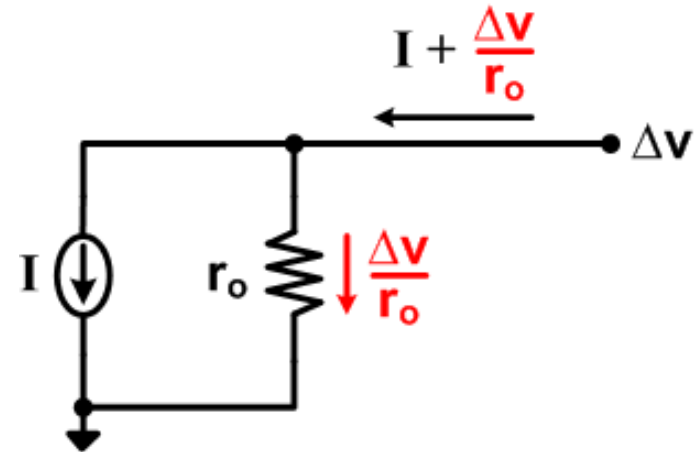
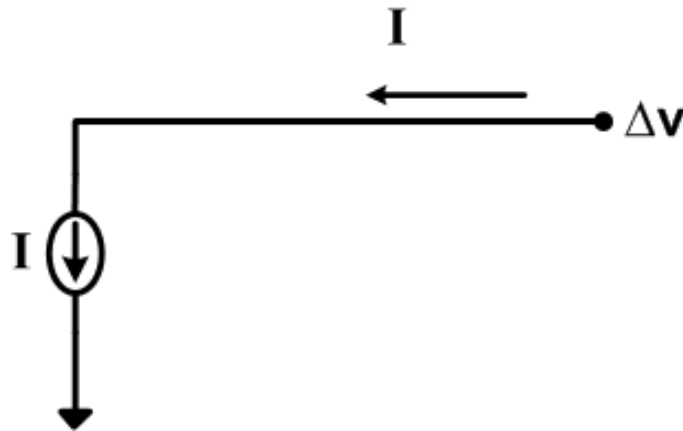
Texas A&M University

Announcements

- HW6 due Apr 25
- Exam 3 Review Session Apr 23 in class
- Exam 3 is May 7 1PM-3PM
 - Primary focus is MOSFET material

Current Source Properties

- Output Resistance



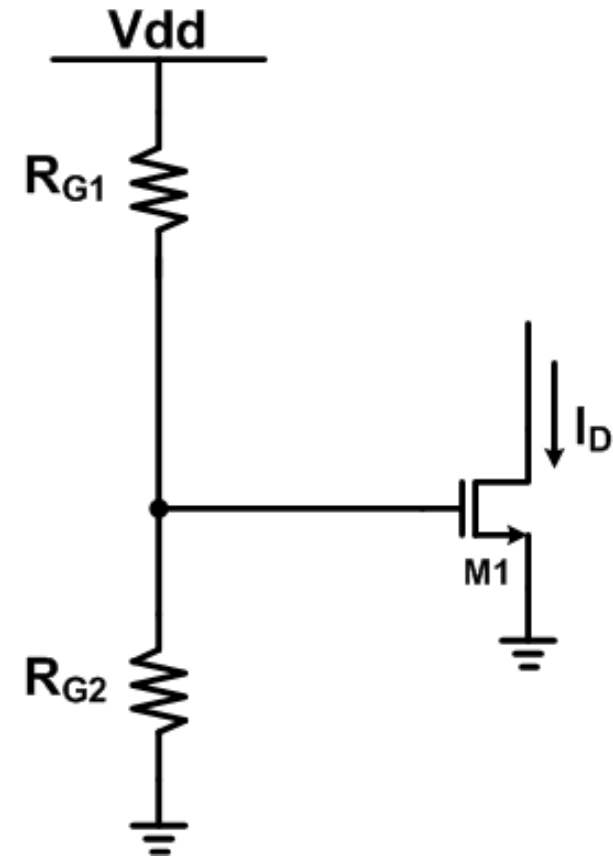
- Finite output resistance degrades current source accuracy and amplifier gain
- Other important properties:
 - Voltage headroom (compliance voltage)
 - Accuracy
 - Noise

How Should We Bias Our Circuits?

- Resistive Biasing
 - Assuming saturation

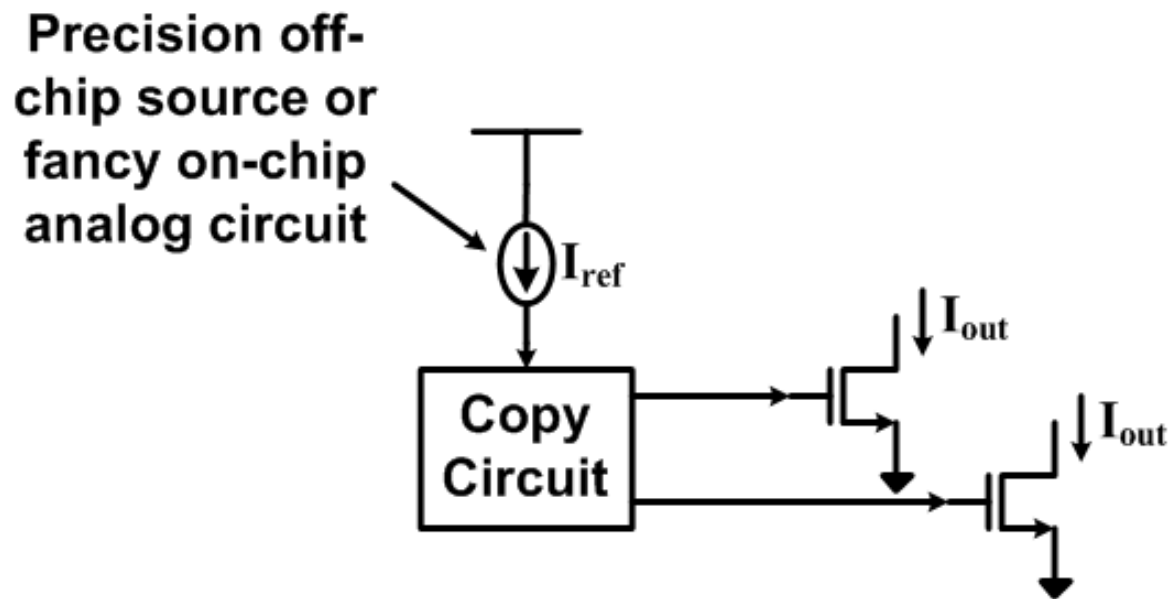
$$I_D = \frac{1}{2} \mu_n C_{ox} \frac{W}{L} (V_G - V_{Tn})^2$$
$$= \frac{1}{2} \mu_n C_{ox} \frac{W}{L} \left(\frac{R_{G2}}{R_{G1} + R_{G2}} V_{dd} - V_{Tn} \right)^2$$

- I_D is sensitive to
 - Supply (V_{dd})
 - Process (V_{Tn} and $\mu_n C_{ox} W/L$)
 - Temperature (V_{Tn} and μ_n)



IC Biasing

- In IC design we often assume that we have **one** precise current source and we copy its value to our circuits



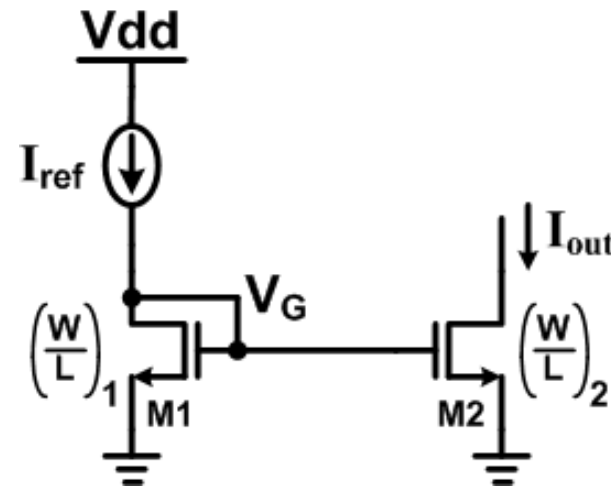
Simple Current Mirror

- That copy circuit is a current mirror
- Simple Current Mirror

What is V_G ?

$$I_D = I_{REF} = \frac{1}{2} \mu_n C_{ox} \left(\frac{W}{L} \right)_1 (V_G - V_{Tn})^2$$

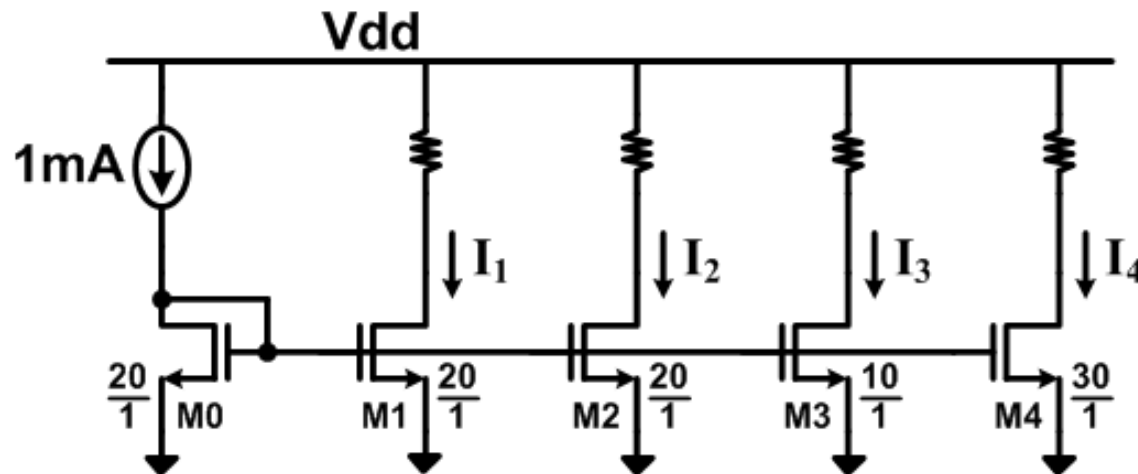
$$V_G = \sqrt{\frac{2I_{REF}}{\mu_n C_{ox} \left(\frac{W}{L} \right)_1}} + V_{Tn}$$



- If V_G is applied to another transistor

$$I_{out} = \frac{1}{2} \mu_n C_{ox} \left(\frac{W}{L} \right)_2 \left(\sqrt{\frac{2I_{REF}}{\mu_n C_{ox} \left(\frac{W}{L} \right)_1}} + V_{Tn} - V_{Tn} \right)^2 \rightarrow I_{out} = \frac{\left(\frac{W}{L} \right)_2}{\left(\frac{W}{L} \right)_1} I_{REF}$$

Ideal Current Mirror Example



$$I_1 = 1\text{mA}$$

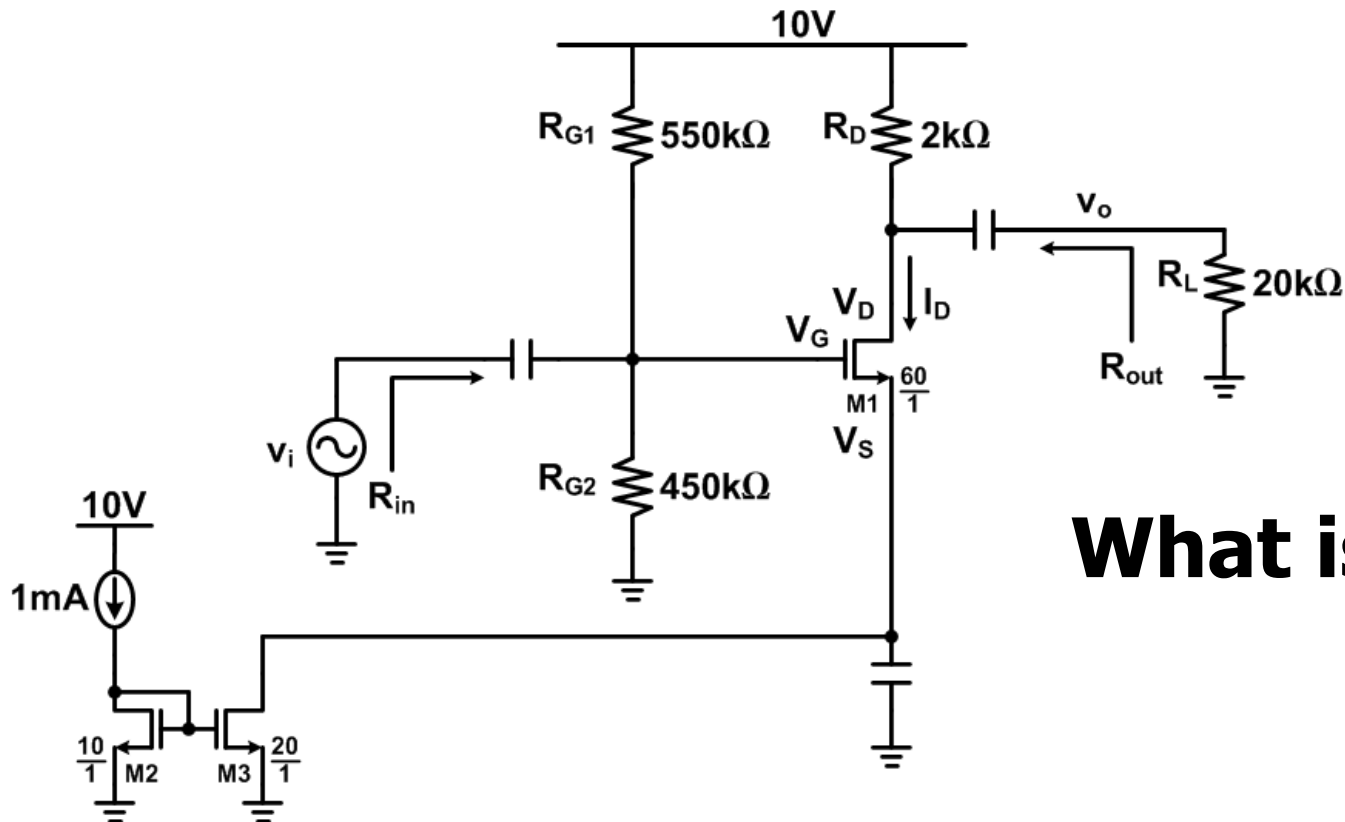
$$I_2 = 1\text{mA}$$

$$I_3 = 0.5\text{mA}$$

$$I_4 = 1.5\text{mA}$$

- This bias scheme reduces sensitivity to process, voltage, and temperature variations

CS Amplifier w/ Current Source



What is I_D ?

- Need to insure that M3 remains in saturation

$$V_s = V_G - (V_{ov1} + V_{Tn}) = \left(\frac{R_{G2}}{R_{G1} + R_{G2}} \right) V_{dd} - \left(\sqrt{\frac{2I_D}{\mu_n C_{ox} \left(\frac{W}{L} \right)_1}} + V_{Tn} \right)$$